





The HMC599ST89(E) is ideal for:

- VHF / UHF Antennas
- HDTV Receivers
- CMTS Equipment
- CATV, Cable Modem & DBS

Functional Diagram



GaAs pHEMT MMIC LNA, 75 Ohm 50 - 1000 MHz

Features

High P1dB Output Power: +19 dBm High Output IP3: +39 dBm Low Noise Figure: 2.2 dB Cascadable 75 Ohm I/Os Single Bias Supply: +3V or +5V Industry Standard SOT89 Package

General Description

The HMC599ST89(E) is a GaAs PHEMT High Linearity, Low Noise Gain Block MMIC SMT amplifier covering 50 to 1000 MHz. Packaged in an industry standard SOT89, the amplifier can be used as a cascadable 75 Ohm RF or IF gain stage as well as a PA or LO driver with up to +19 dBm output power. The HMC599ST89(E) offers 14 dB of gain with a +39 dBm output IP3 at 250 MHz, and can operate directly from a +3V or +5V supply. The HMC599ST89(E) exhibits excellent gain and output power stability over temperature, while requiring a minimal number of external bias components.

Electrical Specifications, Vdd = 5V, T_{a} = +25° C

| Parameter | | Min. | Тур. | Max. | Units |
|---|--------------------------------|----------|------------|------|------------|
| Gain | 50 - 500 MHz 500 - 1000 MHz | 13 12 | 14.5 14 | | dB dB |
| Gain Variation Over Temperature | 50 - 1000 MHz | | 0.005 | | dB/ °C |
| Input Return Loss | 50 - 500 MHz 500 - 1000 MHz | | 15 12 | | dB dB |
| Output Return Loss | 50 - 500 MHz 500 - 1000 MHz | | 25 15 | | dB dB |
| Reverse Isolation | 50 - 1000 MHz | | 20 | | dB |
| Output Power for 1 dB Compression (P1dB) | 50 - 500 MHz | 16 | 19 | | dBm |
| Output Third Order Intercept (IP3) (Pout= -10 dBm per tone, 1 MHz spacing) | 50 - 500 MHz 500 - 1000 MHz | | 39 36 | | dBm dBm |
| Noise Figure | 50 - 1000 MHz | | 2.2 | | dB |
| Supply Current (Idd) | | 100 | 120 | 140 | mA |

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Broadband Gain & Return Loss @ 3V



Gain vs. Temperature @ 3V



Input Return Loss vs. Temperature @ 3V



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GaAs pHEMT MMIC LNA, 75 Ohm 50 - 1000 MHz

Broadband Gain & Return Loss @ 5V



Gain vs. Temperature @ 5V



Input Return Loss vs. Temperature @ 5V



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Output Return Loss vs. Temperature @ 3V



Reverse Isolation vs. Temperature @ 3V



Noise Figure vs. Temperature @ 3V



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Output Return Loss vs. Temperature @ 5V



Reverse Isolation vs. Temperature @ 5V



Noise Figure vs. Temperature @ 5V



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IP3 vs. Temperature @ 3V



P1dB vs. Temperature @ 3V



Psat vs. Temperature @ 3V



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GaAs pHEMT MMIC LNA, 75 Ohm 50 - 1000 MHz

IP3 vs. Temperature @ 5V



P1dB vs. Temperature @ 5V



Psat vs. Temperature @ 5V



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17

16

15

14

13

12

11

10

q

0 0.1 0.2

GAIN (dB)

GaAs pHEMT MMIC LNA, 75 Ohm 50 - 1000 MHz

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P1dB vs. Supply Voltage



Psat vs. Supply Voltage



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Absolute Maximum Ratings

| Drain Bias Voltage (Vdd) | +6 Vdc |
|---|----------------|
| RF Input Power (RFIN) | +10 dBm |
| Channel Temperature | 175 °C |
| Continuous Pdiss (T = 85 °C) (derate 9.84 mW/°C above 85 °C) | 0.89 W |
| Thermal Resistance (junction to ground paddle) | 101.67 °C/W |
| Storage Temperature | -65 to +150 °C |
| Operating Temperature | -40 to +85 °C |

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Typical Supply Current vs. Vdd

| Vdd (Vdc) | ldd (mA) |
|-----------|----------|
| +5 | 120 |
| +3 | 120 |



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

Outline Drawing







NOTES:

1. PACKAGE BODY MATERIAL:

MOLDING COMPOUND MP-180S OR EQUIVALENT.

2. LEAD MATERIAL: Cu w/ Ag SPOT PLATING.

3. LEAD PLATING: 100% MATTE TIN.

4. DIMENSIONS ARE IN INCHES [MILLIMETERS]

ADIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15 mm PER SIDE. DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25 mm PER SIDE. 7. ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.

Package Information

| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking ^[3] |
|-------------|--|---------------|---------------------|--------------------------------|
| HMC599ST89 | Low Stress Injection Molded Plastic | Sn/Pb Solder | MSL1 ^[1] | H599 XXXX |
| HMC599ST89E | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL1 ^[2] | <u>H599</u> XXXX |

[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

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v02.0311

GaAs pHEMT MMIC LNA, 75 Ohm 50 - 1000 MHz



Pin Descriptions

| Pin Number | Function | Description | Interface Schematic | |
|------------|----------|---|---------------------|--|
| 1 | IN | This pin is DC coupled. See the application circuit for off-chip components | | |
| 3 | OUT | RF output and DC Bias (Vdd) for the output stage. | | |
| 2, 4 | GND | These pins and package bottom must be connected to RF/DC ground. | | |

Application Circuit



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Evaluation PCB



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List of Materials for Evaluation PCB 119696 [1]

| Item | Description | |
|---------|------------------------------|--|
| J1 - J2 | PCB Mount 75 Ohm Connector | |
| J3 | DC Pin | |
| C1, C3 | 1000 pF Capacitor, 0603 Pkg. | |
| C2 | 390 pF Capacitor, 0603 Pkg. | |
| C4 | 2.2 µF Capacitor, Tantalum | |
| C5 | 10 KpF Capacitor, 0402 Pkg. | |
| C6 | 0.5 pF Capacitor, 0402 Pkg. | |
| L1 | 0.9 µH Inductor, 1008 Pkg. | |
| L2, L3 | 2.2 nH Inductor, 0603 Pkg. | |
| R1 | 665 Ohm Resistor, 0402 Pkg. | |
| U1 | HMC599ST89 / HMC599ST89E | |
| PCB [2] | 119694 Evaluation PCB | |

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

[3] Evaluation board tuned for 900 MHz operation

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The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.